

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 6,917,093 B2
APPLICATION NO. : 10/691843
DATED : July 12, 2005
INVENTOR(S) : Chen et al.

Page 1 of 2

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

In the drawings:

In the drawings, replace sheet 2 of 2 with the corrected sheet 2 of 2 consisting of Figs. 2-4, as shown on the attached page.

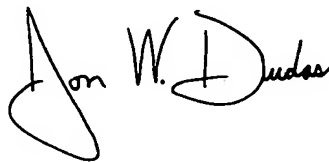
In the specification:

Please replace column 3 lines 12-17 with the following amended paragraph:

Also as shown in Figure 2, photoresist 400 is applied and a STI mask is used to pattern the regions on the wafer surface where a STI trench will be formed. The trench-pattern puts the trench-edges along the <100> direction ~~so that after trench etch~~. The significance of the orientation will be explained in a later paragraph.

Signed and Sealed this

Eighth Day of July, 2008

A handwritten signature in black ink, appearing to read "Jon W. Dudas". The signature is stylized with a large, looped initial "J" and a cursive "Dudas".

JON W. DUDAS
Director of the United States Patent and Trademark Office

U.S. Patent

Jul. 12, 2005

Sheet 2 of 2

6,917,093 B2

FIG. 2

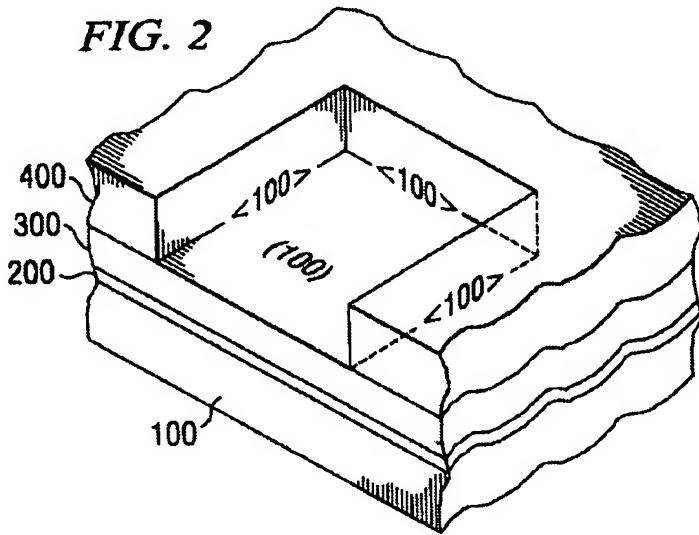


FIG. 3

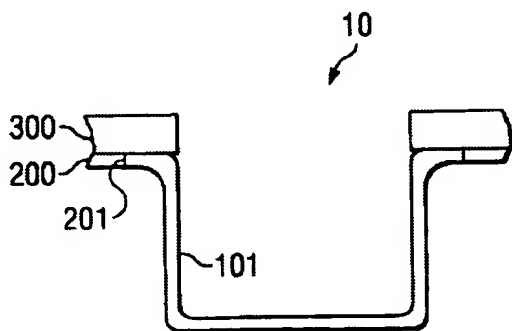
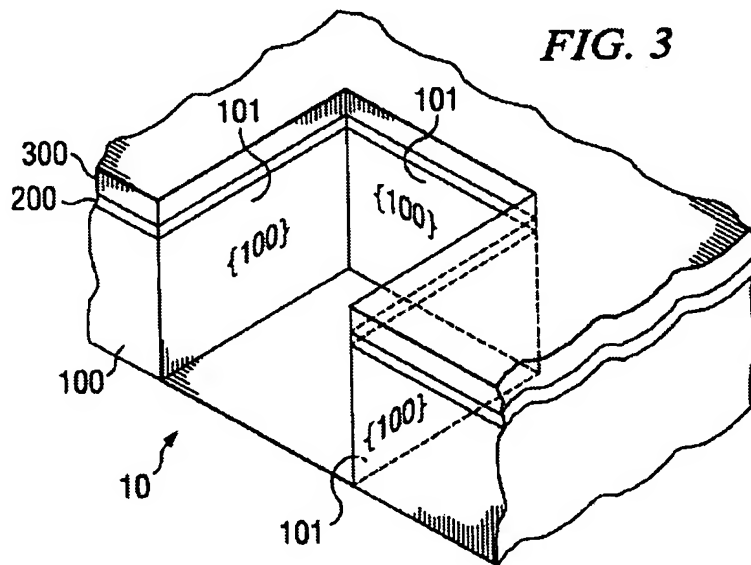


FIG. 4

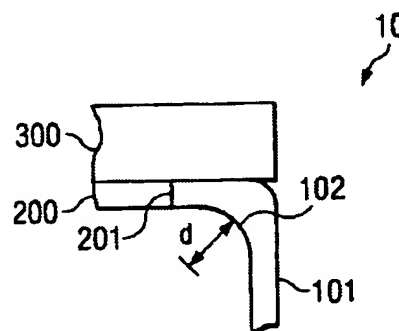


FIG. 5